

1SS373 SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

Features

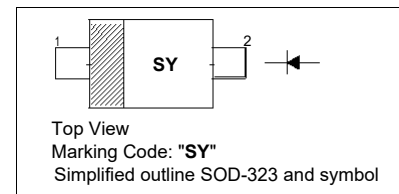
- Low forward voltage

Applications

- High speed switching

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Cathode |
| 2 | Anode |



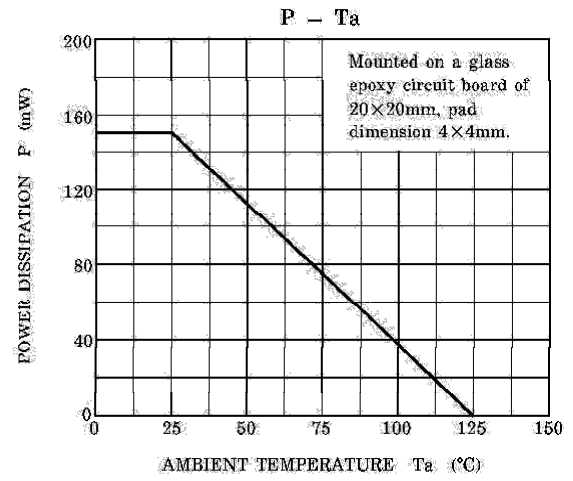
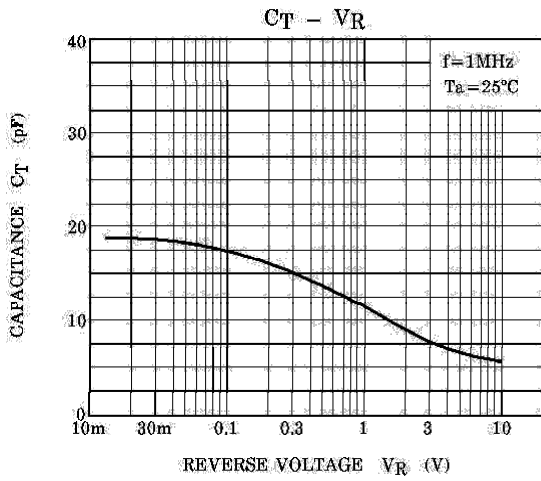
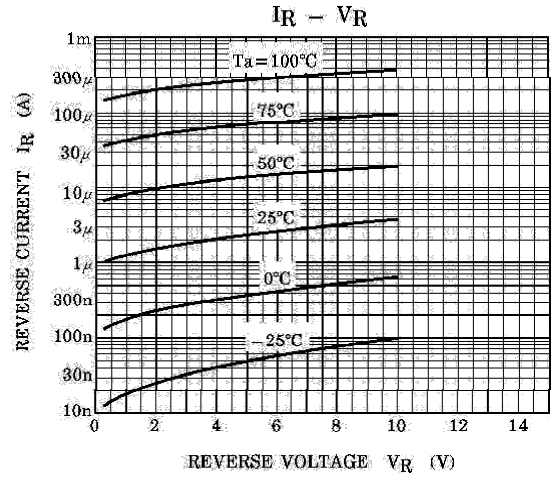
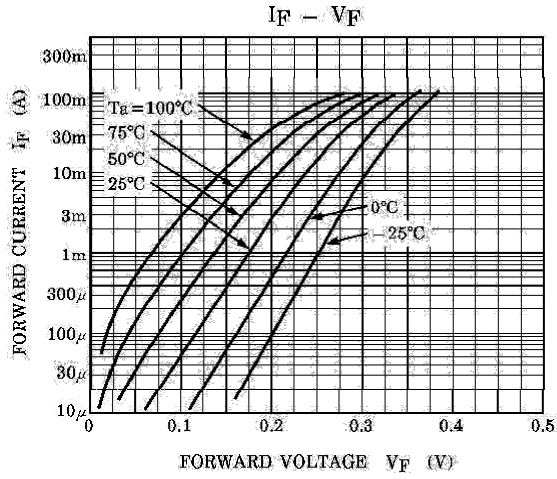
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|--------------------------------|-----------|---------------|------------------|
| Maximum (Peak) Reverse Voltage | V_{RM} | 15 | V |
| Reverse Voltage | V_R | 10 | V |
| Average Forward Current | I_O | 100 | mA |
| Maximum (Peak) Forward Current | I_{FM} | 200 | mA |
| Surge Forward Current (10 ms) | I_{FSM} | 1 | A |
| Power Dissipation | P_{tot} | 150 | mW |
| Junction Temperature | T_J | 125 | $^\circ\text{C}$ |
| Operating Temperature Range | T_{opr} | - 40 to + 100 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | - 55 to + 125 | $^\circ\text{C}$ |

Characteristics at $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Max. | Unit |
|---|--------|------------|---------------|
| Forward Voltage at $I_F = 5\text{ mA}$ at $I_F = 100\text{ mA}$ | V_F | 0.3 0.5 | V |
| Reverse Current at $V_R = 10\text{ V}$ | I_R | 20 | μA |
| Total Capacitance at $f = 1\text{ MHz}$ | C_T | 40 | pF |

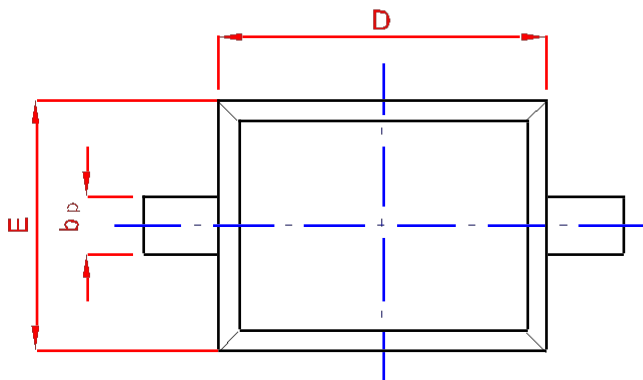
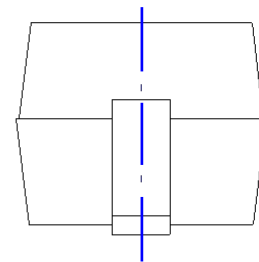
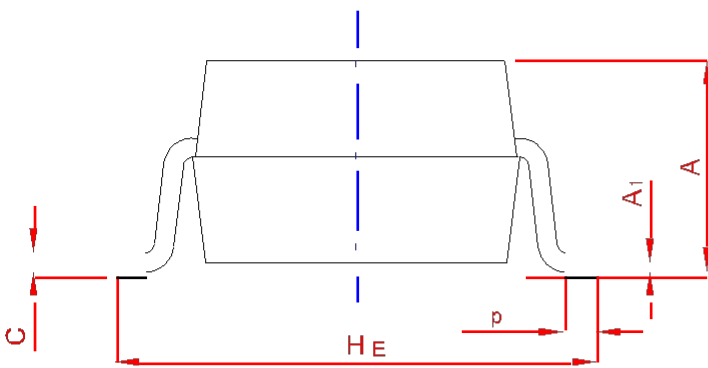
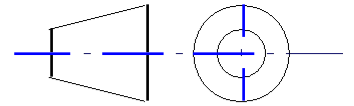
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



| UNIT | A | bp | C | D | E | HE | A1 | Lp |
|------|------|------|------|------|------|------|------|------|
| mm | 1.20 | 0.40 | 0.15 | 1.80 | 1.35 | 2.80 | 0.10 | 0.50 |
| | 0.90 | 0.25 | 0.10 | 1.60 | 1.15 | 2.30 | 0.01 | 0.20 |